VS-16RIA Series

Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 16 A



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PRIMARY CHARACTERISTICS				
I _{T(AV)}	16 A			
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
V _{TM}	1.75 V			
I _{GT}	60 mA			
TJ	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			
Circuit configuration	Single SCR			

FEATURES

- · Improved glass passivation for high reliability and exceptional stability at high temperature
- · High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- · Medium power switching
- Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	ETER TEST CONDITIONS VALUES		UNITS		
1		16	A		
I _{T(AV)}	T _C	85	°C		
I _{T(RMS)}		35	A		
I _{TSM}	50 Hz	340			
	60 Hz	360	A		
l ² t	50 Hz	574	A ² s		
	60 Hz	524	A-S		
V _{DRM} /V _{RRM}		100 to 1200	V		
tq	Typical	110	μs		
TJ		-65 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-16RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

⁽²⁾ For voltage pulses with $t_p \le 5$ ms

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ABSOLUTE MAXIMUM RAT	INGS					
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current at case temperature	I _{T(AV)}	180° sinusoi	180° sinusoidal conduction		16 85	A ℃
Maximum RMS on-state current	I _{T(RMS)}				35	A
	1(1100)	t = 10 ms	No voltage		340	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		360	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{BBM}		285	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	300	
Maximum I ² t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	574	A ² s
	l ² t	t = 8.3 ms			524	
		t = 10 ms	100 % V _{RRM} reapplied		405	
		t = 8.3 ms			375	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied, T _J = T _J maximum		5740	A²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $ _{T(AV)} < l < \pi$ x $ _{T(AV)}$), T _J = T _J maximum		0.97	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J$ maximum			-
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), T _J = T _J maximum			17.9	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			13.6	mΩ
Maximum on-state voltage	V _{TM}	I _{pk} = 50 A, T _J = 25 °C			1.75	V
Maximum holding current	Ι _Η	T _ 05 °C		registive lead	130	
Latching current	١L	$I_{\rm J} = 25^{-1}$ C, 8	$T_J = 25 \text{ °C}$, anode supply 6 V, resistive load			mA

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
$V_{DRM} \le 600$				200	
Maximum rate of rise	$V_{DRM} \leq 800 \ V$	dl/dt	T_J = T_J maximum, V_{DM} = Rated V_{DRM} Gate pulse = 20 V, 15 Ω , t_p = 6 μ s, t_r = 0.1 μ s maximum I_{TM} = (2 x rated dl/dt) A	180	A/µs
of turned-on current	$V_{DRM} \leq 1000 \; V$	ui/ut		160	
	$V_{DRM} \leq 1600 \; V$			150	
Typical turn-on time		t _{gt}	T _J = 25 °C, at rated V _{DRM} /V _{RRM} , T _J = 125 °C	0.9	
Typical reverse recovery time		t _{rr}	T_J = T_J maximum, I_{TM} = $I_{T(AV)},t_p$ > 200 $\mu s,dI/dt$ = - 10 A/ μs	4	μs
Typical turn-off time		tq	T_J = T_J maximum, I_{TM} = $I_{T(AV)},t_p>200~\mu s,V_R$ = 100 V, dI/dt = - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	

Note

+ $t_q = 10 \ \mu s$ up to 600 V, $t_q = 30 \ \mu s$ up to 1600 V available on special request

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/µs		
of off-state voltage	uv/ul	$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	300 (1)	v/µs	

Note

⁽¹⁾ Available with: $dV/dt = 1000 V/\mu s$, to complete code add S90 i.e. 16RIA120S90

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TRIGGERING					
PARAMETER	SYMBOL	TES	TEST CONDITIONS		UNITS
Maximum peak gate power	P _{GM}			8.0	w
Maximum average gate power	P _{G(AV)}	$T_{J} = T_{J} maximum$		2.0	
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum		1.5	А
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum		10	V
	I _{GT}	T _J = - 65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	mA
DC gate current required to trigger		T _J = 25 °C		60	
		T _J = 125 °C		35	
	V _{GT}	T _J = - 65 °C		3.0	v
DC gate voltage required to trigger		T _J = 25 °C		2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	$T_J = T_J$ maximum, $V_{DRM} =$ Rated value		2.0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum,$ $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	v

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL TEST CONDITIONS VALUES		UNITS		
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to +125		°C
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation 0.86		86	K/W
Maximum thermal resistance, case to heat sink	R _{thCS}	R _{thCS} Mounting surface, smooth, flat and greased 0.35		35	r\/ VV
			TO NUT	TO DEVICE	
				25	lbf · in
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf ∙ m
		(2.8	N·m
Approvimeto weight			1	4	g
Approximate weight			0.	49	oz.
Case style		See dimensions - link at the end of datasheet	t TO-48 (TO-208AA))

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.21	0.15		
120°	0.25	0.25		
90°	0.31	0.34	$T_J = T_J maximum$	K/W
60°	0.45	0.47		
30°	0.76	0.76		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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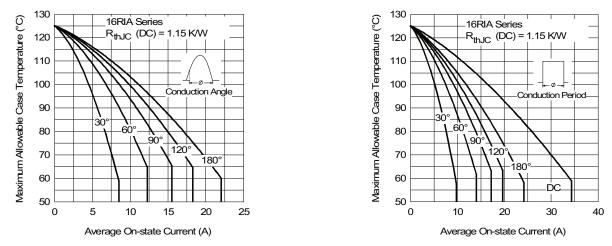
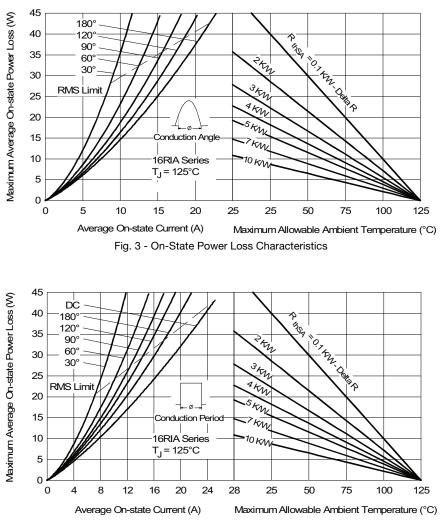


Fig. 1 - Current Ratings Characteristics

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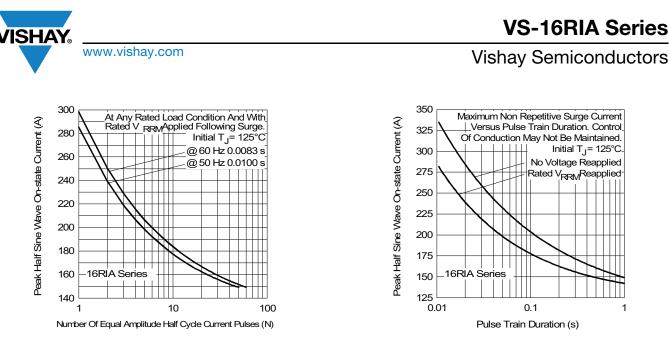
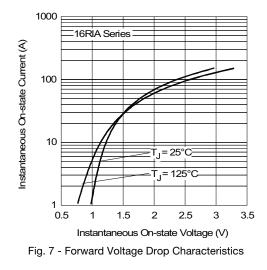


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current



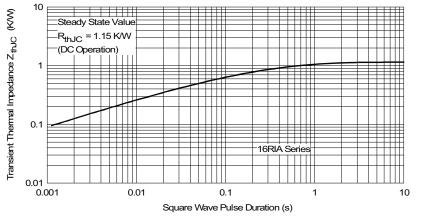


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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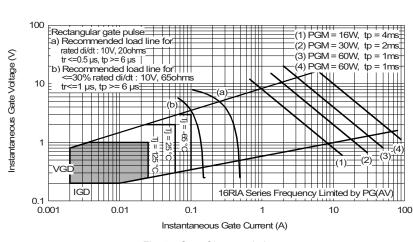
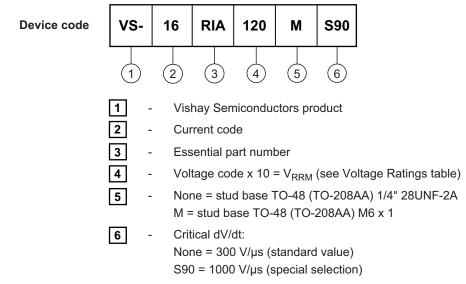


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

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LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95333		

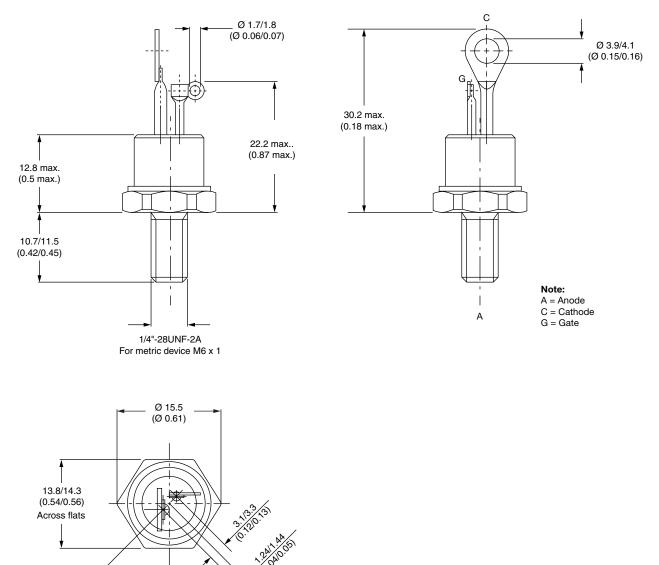


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TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)

45°





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